

Absolute Maximum Ratings (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-200	mA

Thermal Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _d	200	mW
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes: 5. For a device mounted with the collector lead on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 6. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

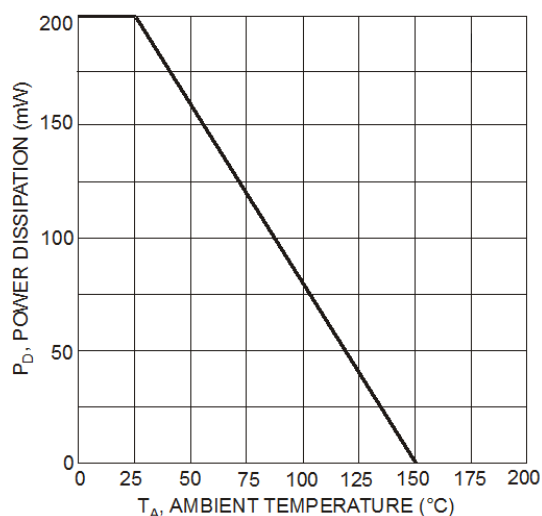
Thermal Characteristics and Derating Information


Fig. 1 Max Power Dissipation vs. Ambient Temperature

Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)					
Collector-Base Breakdown Voltage	BV _{CBO}	-40	—	V	I _C = -10μA, I _E = 0
Collector-Emitter Breakdown Voltage	BV _{CEO}	-40	—	V	I _C = -1mA, I _B = 0
Emitter-Base Breakdown Voltage	BV _{EBO}	-5	—	V	I _E = -10μA, I _C = 0
Collector Cutoff Current	I _{CEX}	—	-50	nA	V _{CE} = -30V, V _{EB(OFF)} = -3V
Base Cutoff Current	I _{BL}	—	-50	nA	V _{CE} = -30V, V _{EB(OFF)} = -3V
ON CHARACTERISTICS (Note 7)					
DC Current Gain	h _{FE}	60 80 100 60 30	— — 300 — —	—	I _C = -100μA, V _{CE} = -1V I _C = -1mA, V _{CE} = -1V I _C = -10mA, V _{CE} = -1V I _C = -50mA, V _{CE} = -1V I _C = -100mA, V _{CE} = -1V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	—	-0.20 -0.30	V	I _C = -10mA, I _B = -1mA I _C = -50mA, I _B = -5mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	-0.65 —	-0.85 -0.95	V	I _C = -10mA, I _B = -1mA I _C = -50mA, I _B = -5mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{OBO}	—	4.5	pF	V _{CB} = -5V, f = 1.0MHz, I _E = 0
Input Capacitance	C _{IBO}	—	10	pF	V _{EB} = -0.5V, f = 1.0MHz, I _C = 0
Input Impedance	h _{IE}	2	12	kΩ	V _{CE} = 1V, I _C = 10mA, f = 1kHz
Voltage Feedback Ratio	h _{RE}	0.1	10	× 10 ⁻⁴	
Small Signal Current Gain	H _{FE}	100	400	—	
Output Admittance	h _{OE}	3	60	μS	
Current Gain-Bandwidth Product	f _T	300	—	MHz	V _{CE} = -20V, I _C = -10mA, f = 100MHz
Noise Figure	NF	—	4	dB	V _{CE} = -5V, I _C = -100μA, R _S = 1kΩ, f = 1kHz
SWITCHING CHARACTERISTICS					
Delay Time	t _d	—	35	ns	V _{CC} = -3V, I _C = -10mA, I _{B1} = -1mA, V _{BE(off)} = 0.5V
Rise Time	t _r	—	35	ns	V _{CC} = -3V, I _C = -10mA, I _{B1} = I _{B2} = -1mA
Storage Time	t _s	—	225	ns	
Fall Time	t _f	—	75	ns	

Note: 7. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

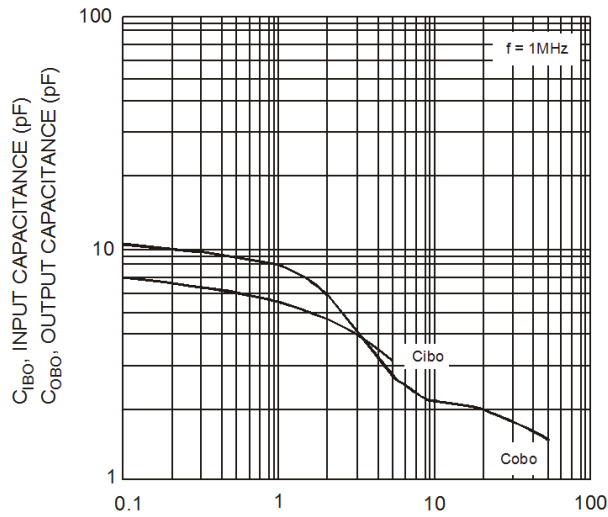


Fig. 2, Input and Output Capacitance vs. Collector-Base Voltage

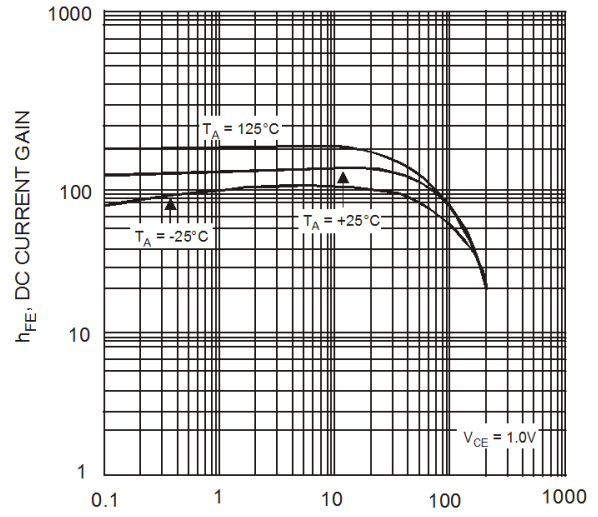


Fig. 3, Typical DC Current Gain vs Collector Current

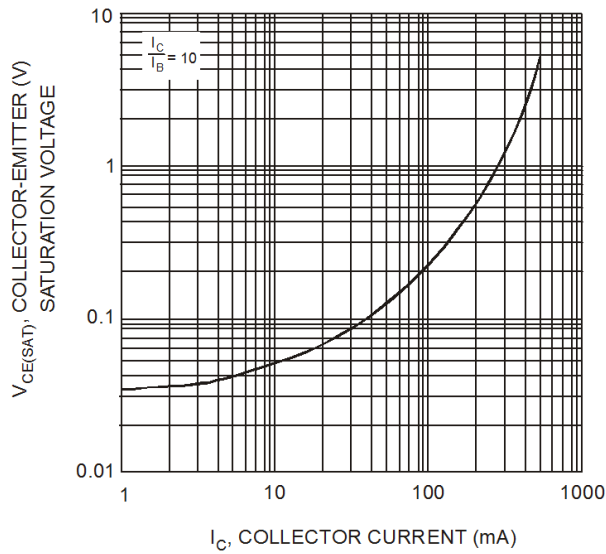


Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current

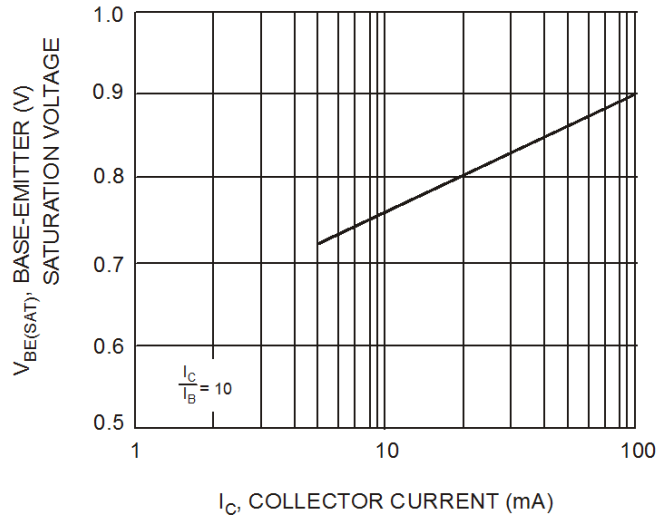
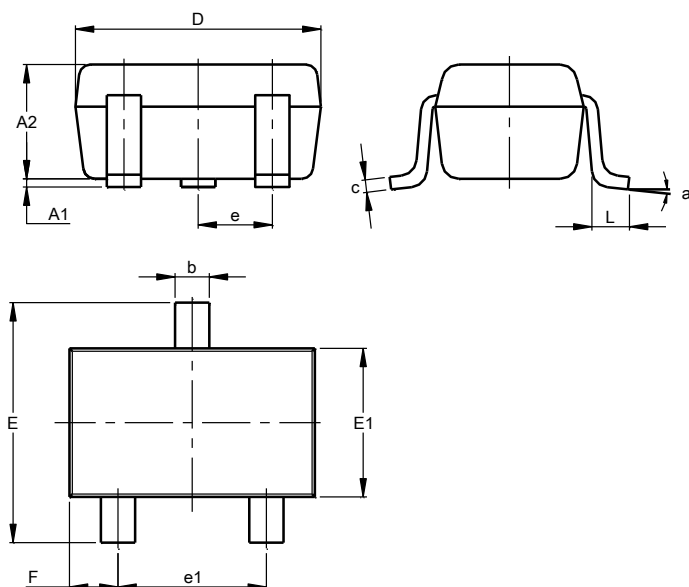


Fig. 5, Typical Base-Emitter Saturation Voltage vs. Collector Current

Package Outline Dimensions

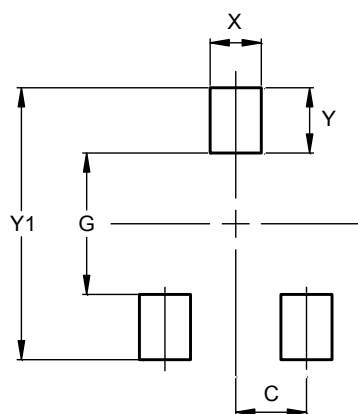
Please see <http://www.diodes.com/package-outlines.html> for the latest version.



SOT323			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.25	0.40	0.30
c	0.10	0.18	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
e1	1.20	1.40	1.30
F	0.375	0.475	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500

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